

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (U-MOS II)

TPCS8205

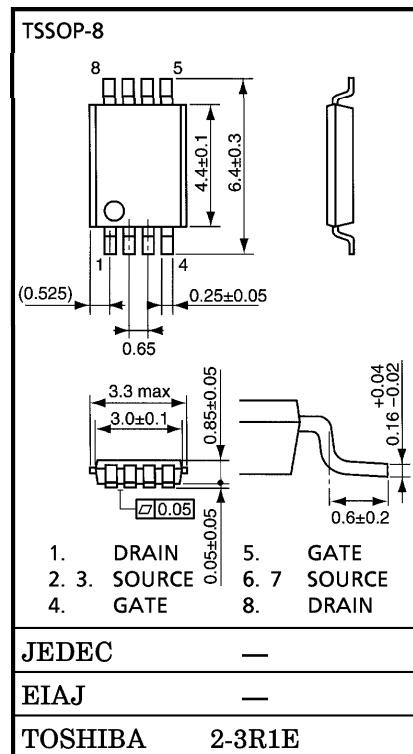
LITHIUM ION BATTERY
 NOTE BOOK PC
 PORTABLE MACHINES AND TOOLS

INDUSTRIAL APPLICATIONS
 Unit in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 30\text{ m}\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 10\text{ S}$ (Typ.)
- Low Leakage Current : $I_{DSS} = 10\text{ }\mu\text{A}$ (Max) ($V_{DS} = 20\text{ V}$)
- Enhancement-Mode : $V_{th} = 0.5\sim 1.2\text{ V}$ ($V_{DS} = 10\text{ V}$, $I_D = 200\text{ }\mu\text{A}$)

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	20	V
Drain-Gate Voltage ($R_{GS} = 20\text{ k}\Omega$)	V_{DGR}	20	V
Gate-Source Voltage	V_{GSS}	± 12	V
Drain Current	DC	I_D	5 A
	Pulse	I_{DP}	20 A
Drain Power Dissipation*** ($T_a = 25^\circ\text{C}$)	P_D	1.0	W
Single Pulse Avalanche Energy*	E_{AS}	32.5	mJ
Avalanche Current	I_{AR}	5	A
Repetitive Avalanche Energy**	E_{AR}	0.1	mJ
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-55\sim 150$	$^\circ\text{C}$



THERMAL CHARACTERISTICS

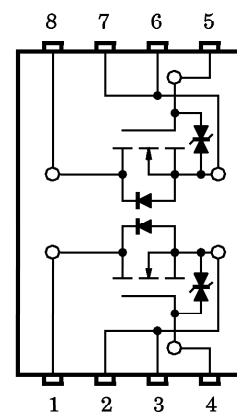
CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Ambient***	$R_{th(ch-a)}$	125	$^\circ\text{C}/\text{W}$

Note ;

- * $V_{DD} = 16\text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 1.0\text{ mH}$, $I_{AR} = 5\text{ A}$, $R_G = 25\text{ }\Omega$
- ** Repetitive rating ; Pulse Width Limited by Max. junction temperature.
- *** Drive operation ; Mount on glass epoxy board [$1\text{ inch}^2 \times 0.8\text{ t}$] in the two devices driving ($t = 10\text{ s}$)

This transistor is an electrostatic sensitive device. Please handle with caution.

CIRCUIT CONFIGURATION



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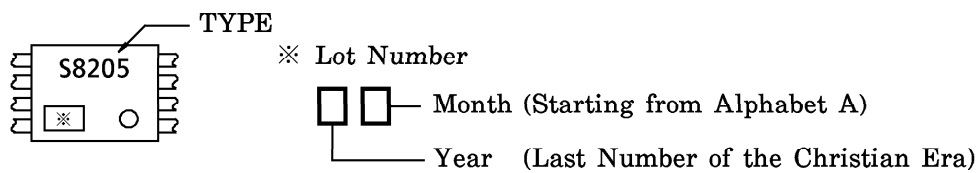
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

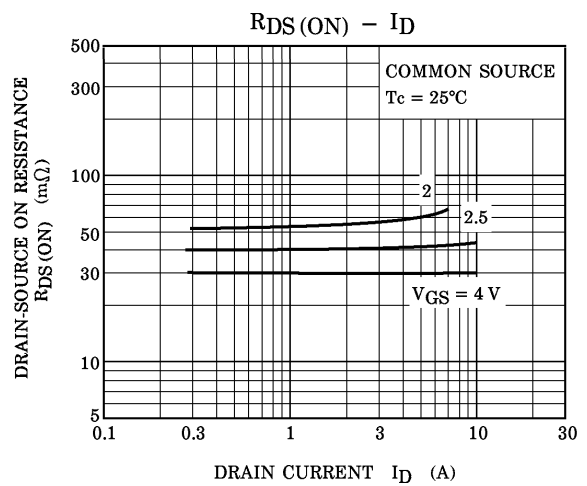
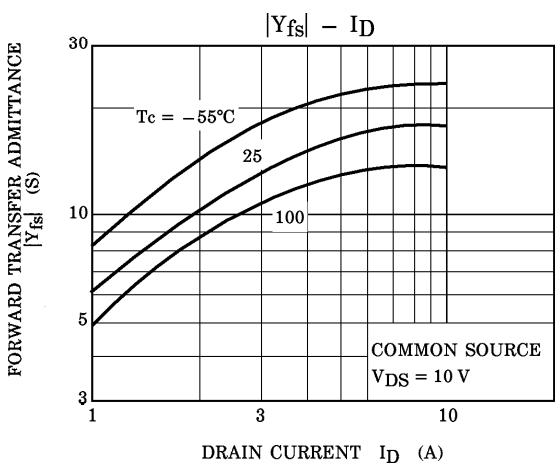
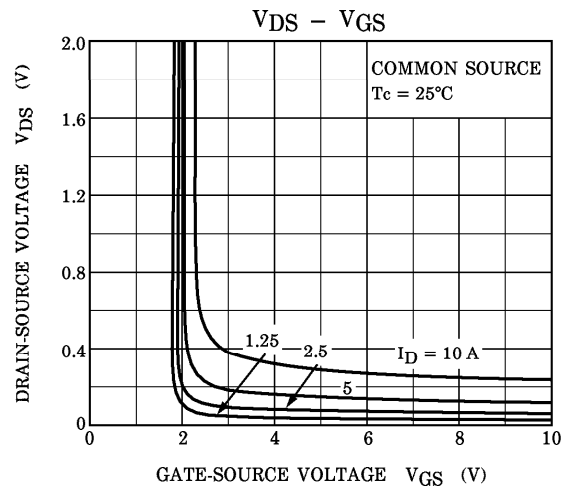
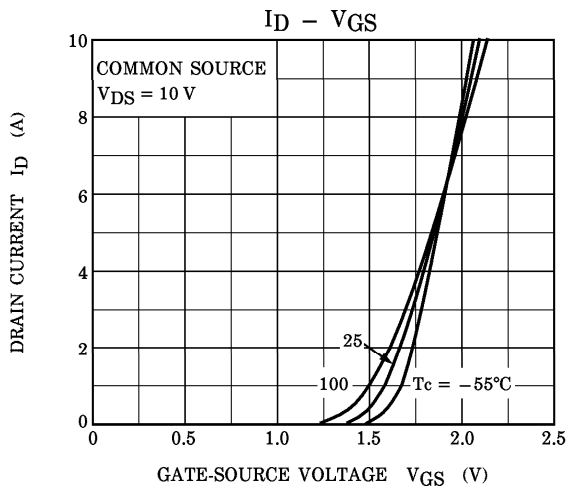
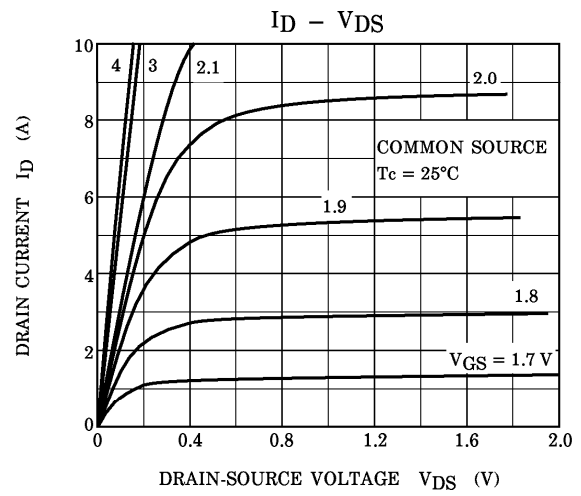
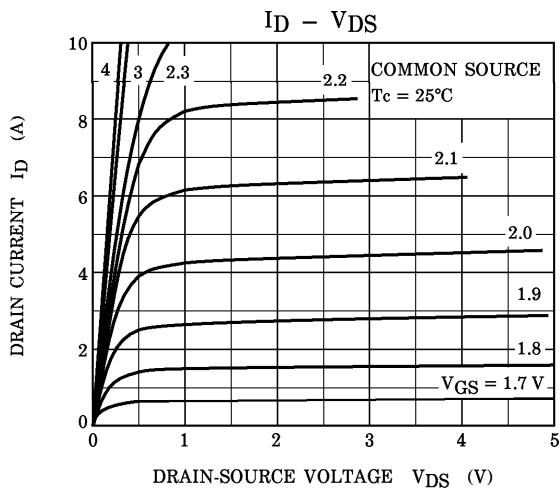
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 10\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 10	μA
Drain Cut-Off Current		I_{DSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$	—	—	10	μA
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	20	—	—	V
		$V_{(BR)DSX}$	$I_D = 10\text{ mA}, V_{GS} = -12\text{ V}$	8	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = 10\text{ V}, I_D = 200\ \mu\text{A}$	0.5	—	1.2	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = 2.0\text{ V}, I_D = 3.5\text{ A}$	—	60	90	$\text{m}\Omega$
		$R_{DS(ON)}$	$V_{GS} = 2.5\text{ V}, I_D = 3.5\text{ A}$	—	40	60	$\text{m}\Omega$
		$R_{DS(ON)}$	$V_{GS} = 4\text{ V}, I_D = 4\text{ A}$	—	30	45	$\text{m}\Omega$
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 2.5\text{ A}$	5	10	—	S
Input Capacitance		C_{iss}	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$	—	760	—	pF
Reverse Transfer Capacitance		C_{rss}		—	110	—	
Output Capacitance		C_{oss}		—	130	—	
Switching Time	Rise Time	t_r	<p>$I_D = 2.5\text{ A}$ $V_{GS} = 5\text{ V}, 0\text{ V}$ $R_L = 4\ \Omega$ $V_{DD} \doteq 10\text{ V}$</p>	—	7	—	ns
	Turn-On Time	t_{on}		—	13	—	
	Fall Time	t_f		—	13	—	
	Turn-Off Time	t_{off}		$V_{IN} : t_r, t_f < 5\text{ ns}$ $\text{Duty} \leq 1\%, t_w = 10\ \mu\text{s}$	—	49	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} \doteq 16\text{ V}, V_{GS} = 5\text{ V}$ $I_D = 5\text{ A}$	—	11	—	nC
Gate-Source Charge		Q_{gs}		—	8	—	
Gate-Drain (“Miller”) Charge		Q_{gd}		—	3	—	

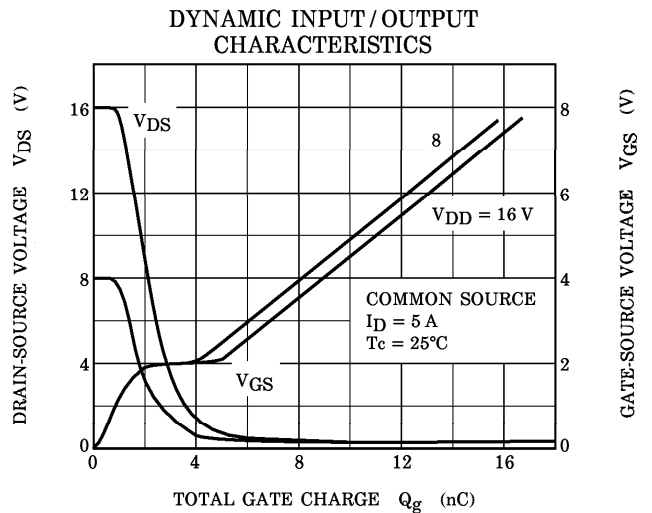
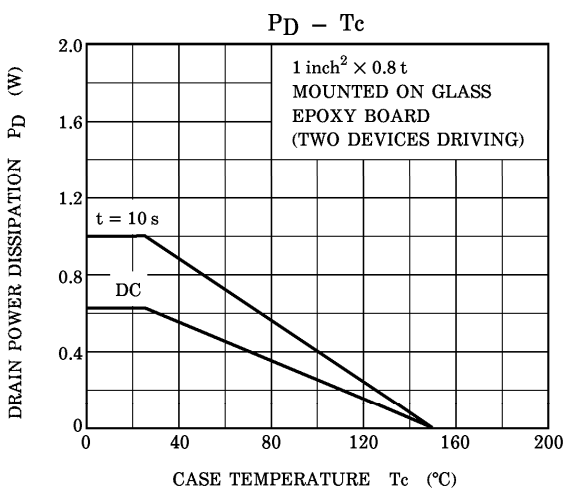
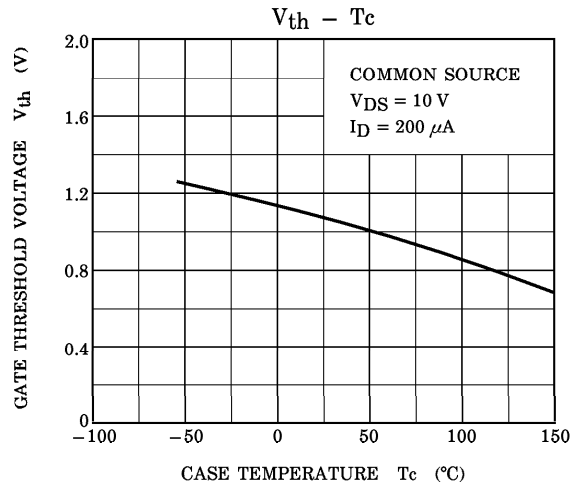
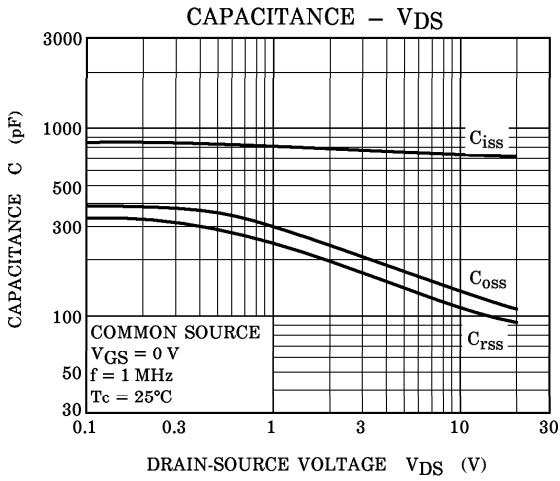
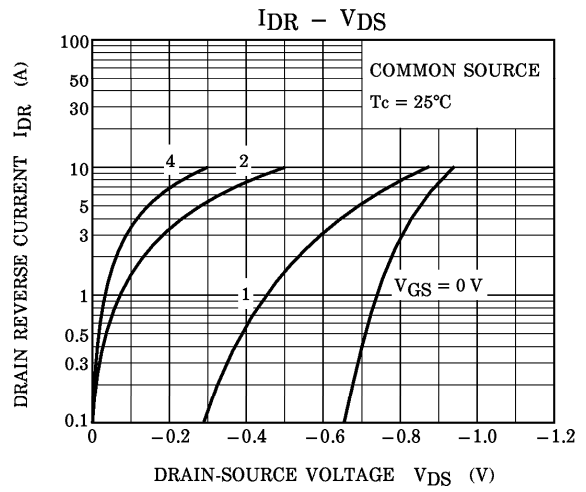
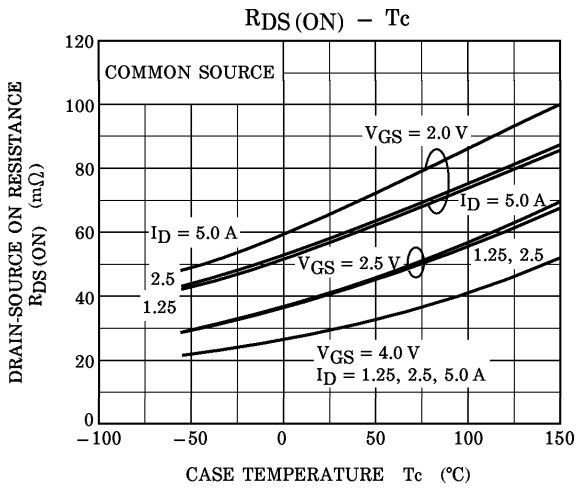
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

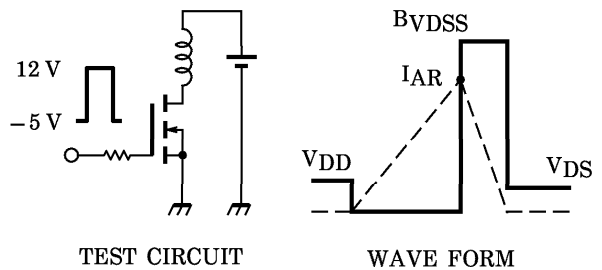
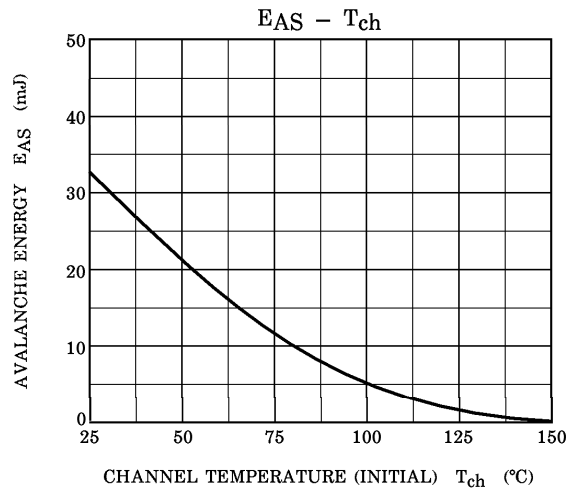
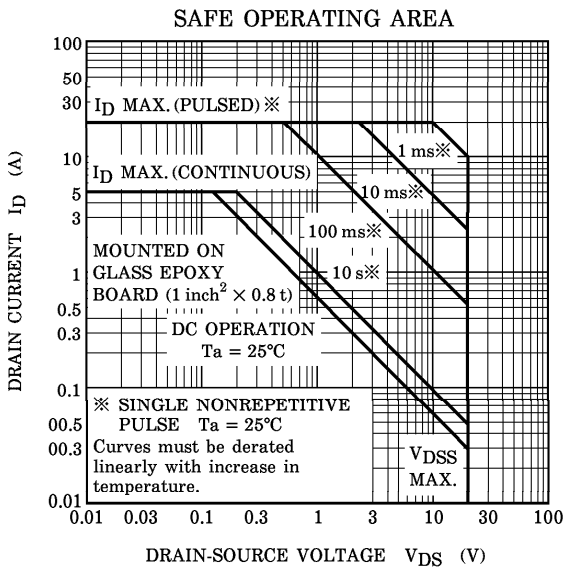
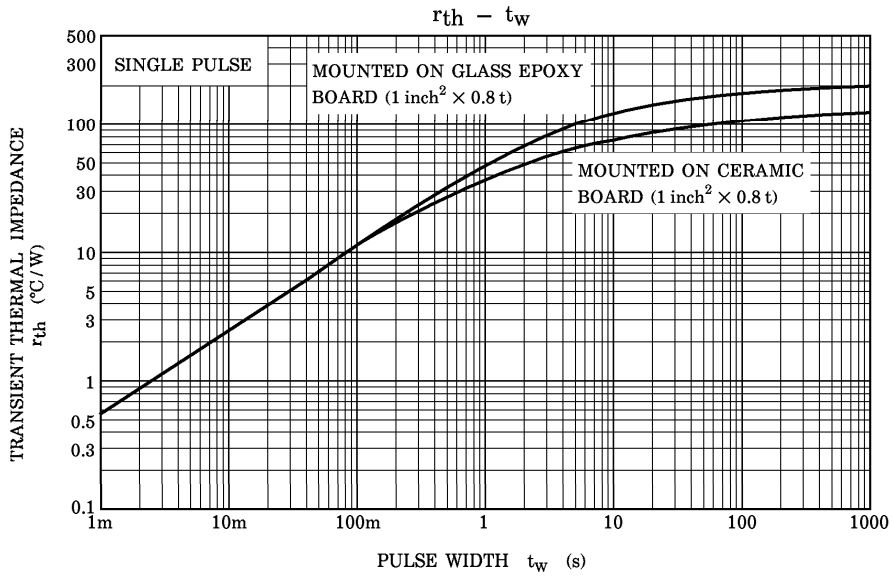
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	5	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	20	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 5\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.2	V

MARKING









Peak $I_{AR} = 5 \text{ A}$, $R_G = 25 \Omega$
 $V_{DD} = 16 \text{ V}$, $L = 1.0 \text{ mH}$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - V_{DD}} \right)$$